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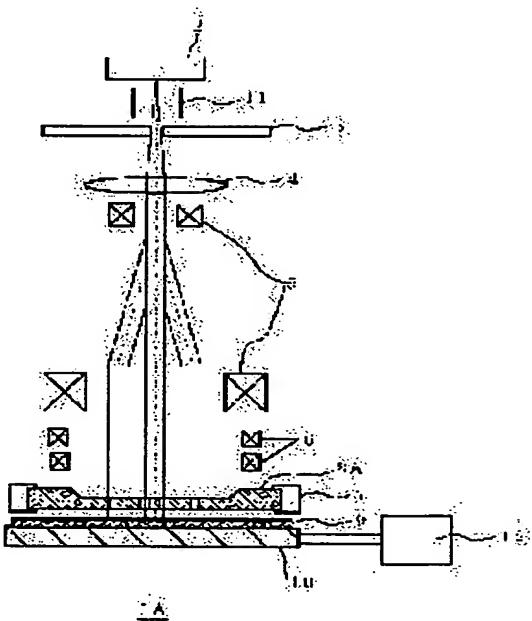
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(54) ELECTRON BEAM EXPOSURE METHOD AND APPARATUS THEREOF

(57)Abstract:

PROBLEM TO BE SOLVED: To execute exposure in electron beam exposure without replacing a mask by allowing the coexistence of complementary masks in one piece of mask or the coexistence of mask patterns, for patterning a plurality of layers constituting a semiconductor element in one piece of mask.

SOLUTION: In an electron beam exposure method for exposing a work such as a wafer 9, etc., by an electron beam through a mask 8A, a mask in which mask patterns are arranged on respective regions of an exposure region of the mask 8A divided into (n) pieces is used, exposure is repeated (n) times to expose the entire region to be exposed, and the work is moved for every exposure by each region corresponding to the regions to be processed which are divided into (n) pieces.



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